

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device including: providing a substrate having an insulating layer and a single crystal silicon layer formed on the insulating layer; forming a strain-inducing semiconductor layer on the single crystal silicon layer, the strain-inducing semiconductor having the lattice constant differing from the lattice constant of the single crystal silicon layer; changing the single crystal silicon layer into a strained silicon layer by matching a lattice of the single crystal silicon layer with a lattice of the strain-inducing semiconductor layer; and removing the strain-inducing semiconductor layer.

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